conductor layer and a Schottky barrier diode including the Schottky junction are connected in parallel between the first main electrode and the second main electrode.

20. The device according to claim 19, wherein one of the second semiconductor layer in a unit cell of the periodical

arrangement structure made of the second semiconductor layer and the third semiconductor layer is shared between the transistor and the Schottky barrier diode as a drift layer.

\* \* \* \* \*